



UNIVERSITI PUTRA MALAYSIA

**CORRELATION OF SOME DIELECTRIC PROPERTIES WITH
PROCESSING AND MICROSTRUCTURE IN
Mg-Sn-O SYSTEM**

IFTETAN AHMAD TAHA

FSAS 1999 15

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By

IFTETAN AHMAD TAHA

**Thesis Submitted in Fulfilment of the Requirements for the Degree of Master of
Science in the Faculty of Science and Environmental Studies,
Universiti Putra Malaysia**

February, 1999



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**MASTER OF SCIENCE
UNIVERSITI PUTRA MALAYSIA**

1999



To:

My Parents

Husband

And

Sisters.



ACKNOWLEDGEMENTS

Firstly, I am very grateful to “ ALLAH ” S.w.t. for giving me the strength, and patient, to complete this research within the specified time.

It is my pleasure to extend my sincere gratitude and indebtedness to Dr. Abdul-Majeed Azad for his continuous supervision, help, and fruitful discussion, without him this research will never be completed. Also I want to express my acknowledgement to my co-supervisor Associate Professor Dr. Abdul Halim Shaari, for his assistance and support during this research. I am also pleased to thank my co-supervisor Dr. Jamil Suradi for his encouragement and support.

I would also like to thank Dr. Mansor Hashim for his kind assistance, encouragement, support and providing the facilities used in this research which enable me to complete the research.

I would like to express my sincere gratitude to Mr. Saleh Al-Khawaldeh and Mrs. Noorhana Yahya for their assistance, discussion and moral support. I would like to thank all the undergraduate students in the materials science group for their friendly co-operation; also I want to thank all postgraduate students in the ferrite group and the superconductor group.

I want to thank Ms. Azilah Abdul Jalal (SEM unit, UPM) for her help during SEM analysis, special thank to Mr. Sri jegan (Chemistry Department, UPM) for his generosity and assistance.

Special thanks are due to my friend Mrs. Fars for her courage to continue this research with patient, and to all my Iraqi friends who encourage me to continue and complete my study.



My very special thanks goes to my family in Iraq, my father Prof. Ahmad Al-Haje Taha from Mosul University, Iraq, my mother for her praying for me and my kids, my lovely sisters and my brother in law for their support from far.

Finally, I want to thank my husband Dr. Waleed A. Thanoon for his generous support and assistance during my studies. Thanks to my kids Dalia, Kaldoon and Zadoon for the time they missed their mother.



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LIST OF ABBREVIATIONS

λ	Wave Length
a, b, c	Lattice parameters
d_{hkl}	Reciprocal d vector
hkl	Miller indices
XRD	X-ray diffraction
SEM	Scanning Electron Microscopy
f, ω	Frequency and angular frequency
A	Cross Sectional Area
θ	Bragg angle
$\tan \delta$	Loss tangent
PVA	Polyvinyl alcohol
T	Temperature
TCC	Temperature Coefficient of Capacitance
TCK	Temperature Coefficient of Dielectric
K	Dielectric Constant
Cp	Capacitor
Gp	Conductor
logC	Logarithm of Capacitance
logf	Logarithm of Frequency
C	Capacitance
Tc	Critical Temperature



P	Pressure
t	Time
D	Diffusivity
$\beta_{1/2}$	Full width Half Maximum
I	Current
ϵ_0	Permittivity of Vacuum
V	Applied Voltage
EDAX	Energy Dispersive Analysis by X-ray
Z	Impedance
M	Modulus
Y	Admittance
LP/CPA	Lumped Parameter /Complex Plane Analysis
α	Coefficient of Linear Thermal Expansion
ρ	Density
m	Mass
M ₂ S	Mg ₂ SnO ₄
MS	MgSnO ₃
AC	Alternating Current
ppm	Part per million

Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirements for the degree of Master of Science.



P	Pressure
t	Time
D	Diffusivity
$\beta_{1/2}$	Full width Half Maximum
I	Current
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February 1999

Chairman: Abdul-Majeed Azad, Ph.D./ Mansor Hashim Ph.D.

Faculty: Science and Environmental Studies

The alkaline-earth stannates having the general chemical formula $M\text{SnO}_3$ ($M = \text{Ca, Sr and Ba}$), have been projected as potential electronic ceramics (thermally stable capacitors, humidity sensor, carbon dioxide sensor, etc.). Even though magnesium is a member of the metal group to which Ca, Sr and Ba belong, no reliable technical information on the compounds in the pseudo-binary MgO-SnO_2 system appears to exist in the published literature. In view of the information gaps in the reported research, vigorous and systematic investigation has been carried out on the MgO-SnO_2 system.

The MgO-SnO_2 system has been thoroughly studied with respect to synthesis, processing and characterisation – physical, microstructural and electrical. Two different synthesis routes have been adopted. These routes are solid-state and self-heat-sustained. For each route two mixtures of different molar ratio viz., 2:1 and 1:1 have



been used. In 2:1 molar ratio mixtures Mg_2SnO_4 has been formed as a single phase upon calcination of starting materials at $1200\text{ }^\circ\text{C}/24\text{ h}$ in both solid-state and self-heat-sustained techniques with one or two impurity peaks at $1200\text{ }^\circ\text{C}/24\text{ h}$. In 1:1 molar ratio, the reaction product consisted of a two-phase mixture of Mg_2SnO_4 and SnO_2 . Evaluation of microstructure that is intimately related to the envisaged properties in the ceramics has been closely and systematically followed as a function of sintering at different temperatures of ($1200\text{-}1600\text{ }^\circ\text{C}$) and soak - time ($2\text{ - }48\text{ h}$).

A thorough analysis of the as measured electrical data showed that the material possessed a very weak temperature dependence of capacitance (TCC) and dielectric constant (TCK) in the range $27\text{-}300\text{ }^\circ\text{C}$ over several decades of frequency domain. It was found that TCC value varied between ($-200\text{ to }+195$) ppm / K thus holding the promise to its usage as a thermally stable capacitor component in high-speed electronic devices. The average dielectric constant was found to be in the range $10\text{-}18$, thus identifying this material as a low dielectric constant system as well.



Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia bagi memenuhi keperluan ijazah Master Sains.

**KORELASI BEBERAPA SIFAT DIELEKTRIK DENGAN PEMROSESAN
DAN MIKROSTRUKTUR DALAM
SISTEM Mg-Sn-O**

Oleh

IFTETAN AHMAD TAHA

Februari 1999

Pengerusi : Abdul-Majeed Azad, Ph.D./ Mansor Hashim, Ph.D.

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Stanat alkali – bumi yang mempunyai formula kimia am $M SnO_3$ ($M = Ca, Sr$ dan Ba) telah diutarakan sebagai seramik elektronik yang berpotensi (kapasitor stabil terma, sensor kelembapan, sensor karbon dioksida dan sebagainya). Walaupun magnesium adalah dalam ahli kumpulan logam yang dipunyai oleh Ca, Sr dan Ba , tidak ada maklumat teknikal yang boleh dipercayai terhadap sebatian itu dalam sistem binari-pseudo $MgO-SnO_2$ yang wujud dalam penulisan yang diterbitkan. Memandangkan terdapatnya jurang maklumat dalam laporan penyelidikan, siasatan secara sistematik dan bersemangat telah dijalankan terhadap sistem $MgO - SnO_2$.

Sistem $MgO-SnO_2$ ini telah dikaji secara menyeluruh terhadap sistesis, pemprosesan dan ciri-ciri fizikal, mikrostruktur dan elektrik. Dua laluan sintesis yang berbeza, iaitu teknik keadaan-pepejal dan tahan-haba-sendiri telah digunakan. Untuk kedua-dua laluan ini, dua campuran molar yang berbeza, dengan nisbah 2:1 dan 1:1 telah disediakan. Dalam campuran nisbah molar 2:1, $Mg_2 SnO_4$ telah terbentuk sebagai fasa tunggal terhadap pemansan bahan awal pada suhu $1200\text{ }^{\circ}\text{C}$ / 24 jam dalam kedua-



dua teknik iaitu keadaan –pepejal dan tahan – haba – sendiri dengan satu atau dua puncak bendasing.

Dalam nisbah molar 1:1, produk tindakbalas terdiri daripada dua fasa campuran $Mg_2 SnO_4$ dan SnO_2 . Penilaian terhadap mikrostruktur yang berkait rapat dengan sifat-sifat jangkaan dalam seramik telah diikuti rapat dan sistematik sebagai fungsi terhadap pensinteran pada suhu yang berbeza iaitu 1200 – 1600 °C selama 2 – 48 jam.

Satu analisis yang terperinci terhadap data pengukuran elektrik menunjukkan bahawa bahan ini memiliki persandaran subu yang amat lemah terhadap kapasitan (PSK) dan pemalar dielektrik (PSD) dalam julat 27 – 300 °C untuk beberapa dekad domain frekuensi. Telah dijumpai juga bahawa nilai KPS berubah antara (-200 kepada +195) ppm / K dan sekaligus memberi jaminan kegunaannya sebagai komponen kapasitor stabil terma dalam peranti elektronik kelajuan – tinggi. Purata pemalar dielektrik yang telah dijumpai adalah dalam julat 10-18, justeru itu juga mengesahkan bahan ini sebagai sistem pemalar dielektrik yang rendah.

CHAPTER I

INTRODUCTION

Relevance / Importance of Electronic Ceramics

Ceramics materials are polycrystalline, inorganic materials which consist of metallic and nonmetallic elements bound together primarily by ionic and / or covalent bonds. The chemical composition of ceramic materials varies considerably, from simple compounds to mixtures of many complex phases bonded together. The earliest use of ceramics was in pottery and bricks (Koller, 1994).

The properties of ceramic materials also vary due to differences in bonding. In general, ceramic materials are typically hard and brittle with low toughness and ductility.

Ceramics are usually good electrical and thermal insulators due to the absence of conduction electrons. They have relatively high melting temperatures and high chemical stability in many hostile environments due to the stability of their strong bonds. In general, ceramics materials used for engineering applications can be divided into two groups: traditional ceramic materials, made

